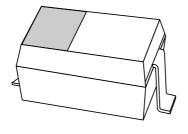
DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG2010EALow V_F MEGA Schottky barrier diode

Product specification

2002 Dec 10





Low V_F MEGA Schottky barrier diode

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FEATURES

Forward current: 1 AReverse voltage: 20 V

• Ultra high-speed switching

· Very low forward voltage

• Very small plastic SMD package.

APPLICATIONS

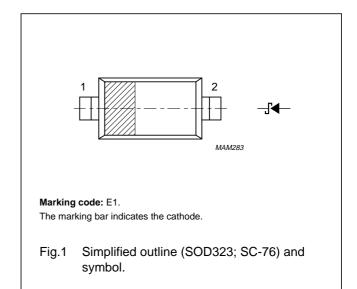
- Ultra high-speed switching
- · Voltage clamping
- · Protection circuits.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOD323 (SC-76) very small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		_	20	V
I _F	continuous forward current		_	1	Α
I _{FSM}	non-repetitive peak forward current	t _p = 8.3 ms half sinewave; JEDEC method	_	5	А
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C

Low V_F MEGA Schottky barrier diode

PMEG2010EA

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	continuous forward voltage	see Fig.2; note 1			
		$I_F = 10 \text{ mA}$	240	270	mV
		I _F = 100 mA	300	350	mV
		$I_F = 1000 \text{ mA}$	480	550	mV
I _R	continuous reverse current	see Fig.3; note 1			
		$V_R = 5 V$	5	10	μΑ
		$V_R = 8 V$	7	20	μΑ
		V _R = 15 V	10	50	μΑ
C _d	diode capacitance	$V_R = 5 V$; $f = 1 MHz$; see Fig.4	19	25	pF

Note

1. Pulsed test: $t_p = 300 \ \mu s$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	note 1	220	K/W
	ambient	note 2	180	K/W

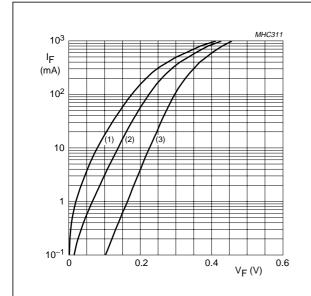
Notes

- 1. Device mounted on an FR4 printed-circuit board with Cu clad 10 x 10 mm.
- 2. Device mounted on an FR4 printed-circuit board with Cu clad 40 x 40 mm.

Low V_F MEGA Schottky barrier diode

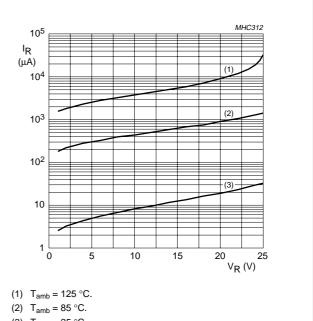
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GRAPHICAL DATA



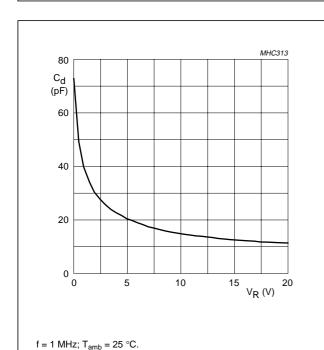
- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



(3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



, and

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

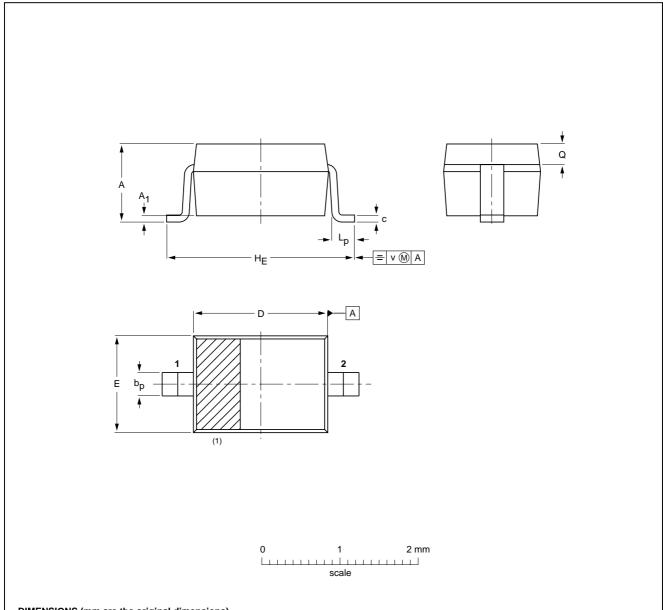
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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD323



DIMENSIONS (mm are the original dimensions)

UNIT	А	A ₁ max.	bp	С	D	E	HE	Lp	Q	v
mm	1.1 0.8	+ 0.05 - 0.05		0.25 0.10	1.8 1.6	1.35 1.15	2.7 2.3	0.45 0.15	0.25 0.15	0.2

Note

1. The marking bar indicates the cathode.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOD323			SC-76			98-09-14 99-09-13	

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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NOTES

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